

Device Modeling Report

COMPONENTS: THYRISTOR
PART NUMBER: BT152-600R
MANUFACTURER: PHILIPS SEMICONDUCTOR



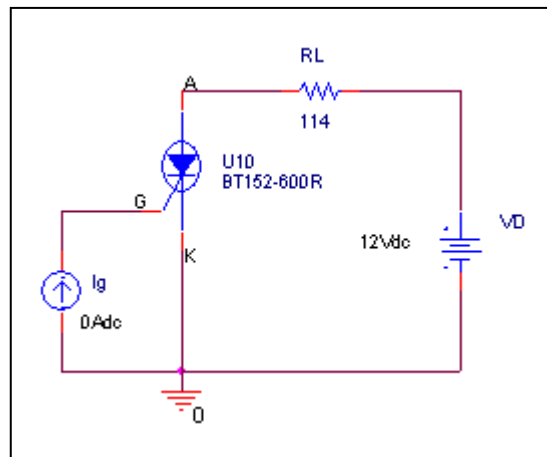
Bee Technologies Inc.

DIODE MODEL

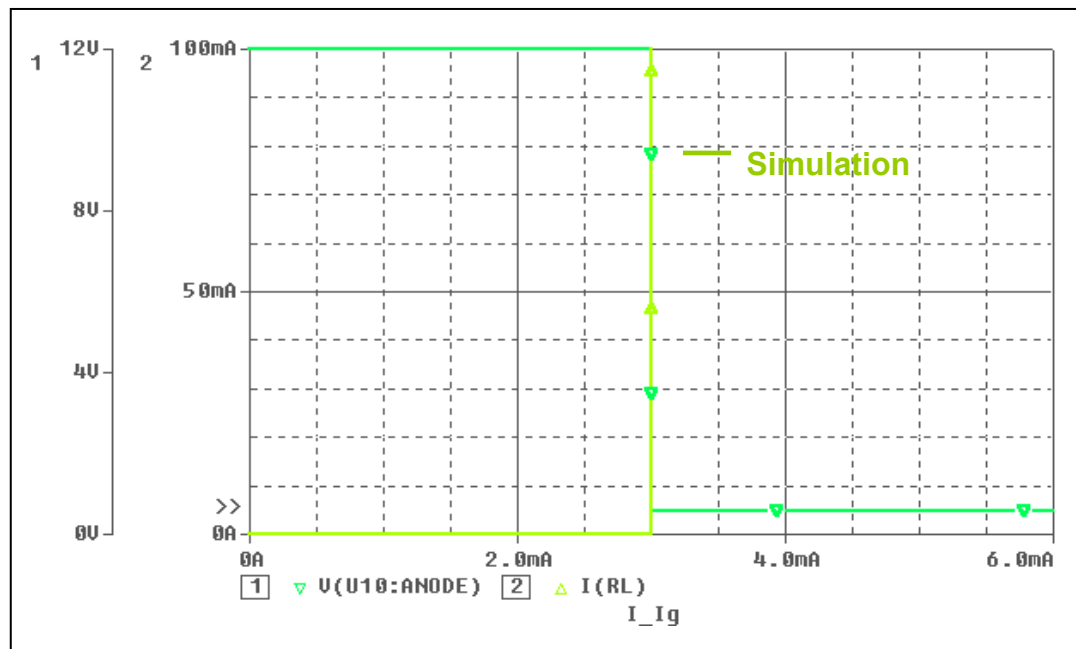
Pspice model Parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

IG-VT Characteristic

Evaluation Circuit



Simulation result

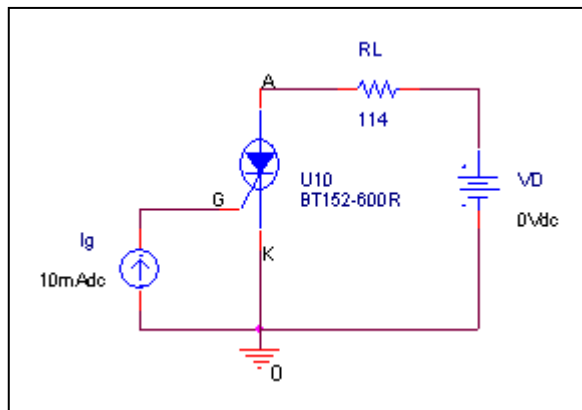


Comparison Table

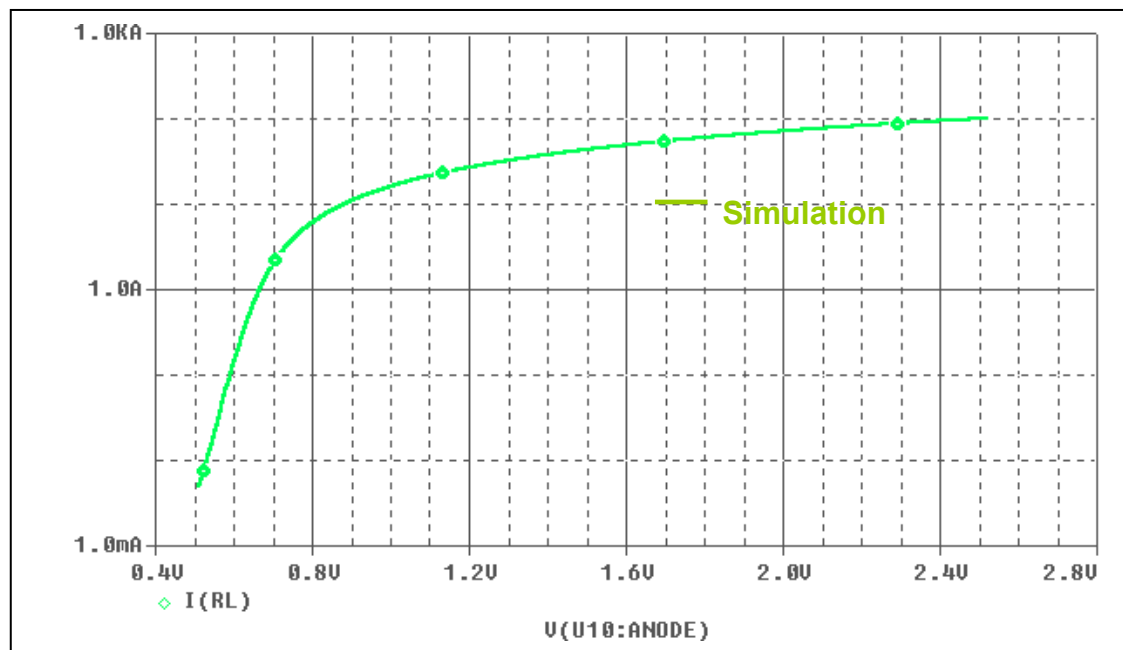
	Measurement	Simulation	% Error
IG_T (mA)	3	2.9804	-0.6533
V_{GT} (V)	0.6	0.591460	-1.4233

ITM-VTM Characteristic

Evaluation Circuit



Simulation result

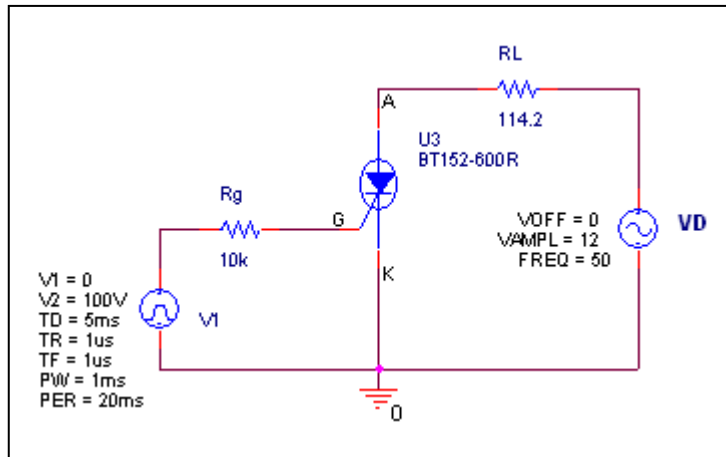


Comparison Table

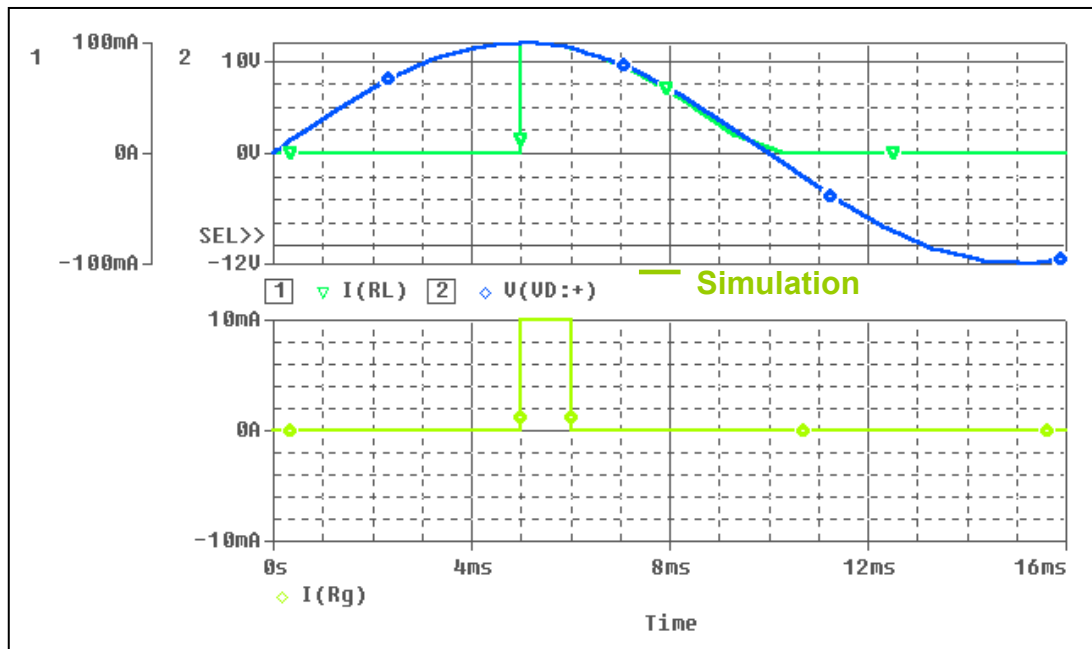
At ITM=40A	Measurement	Simulation	% Error
VTM(V)	1.4	1.4464	3.3143

Holding Characteristic (IH)

Evaluation Circuit



Simulation result

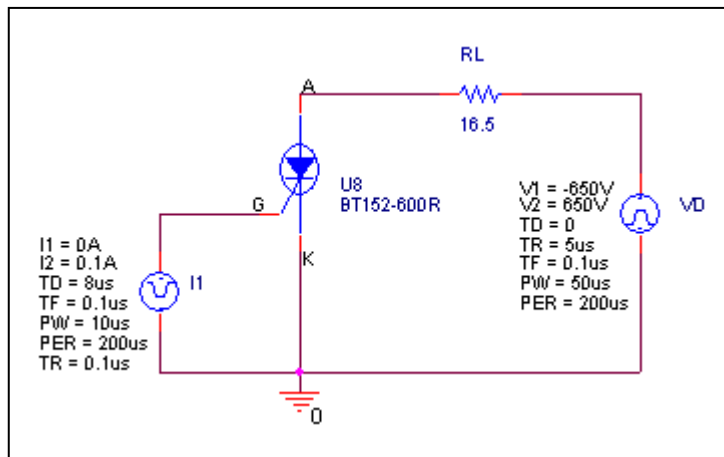


Comparison Table

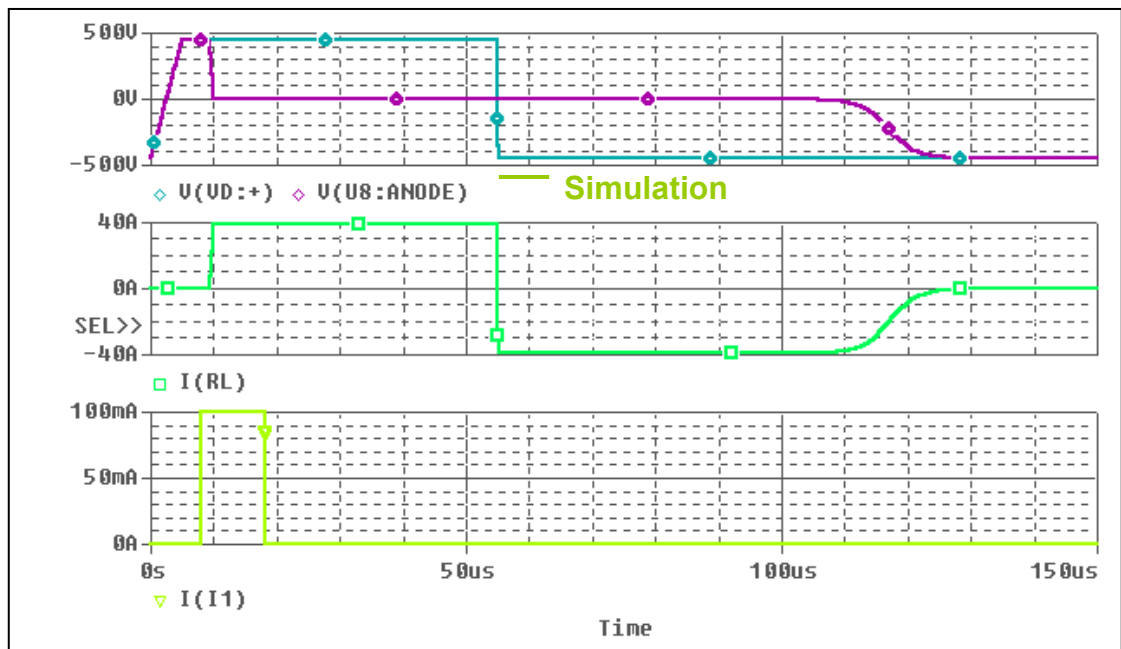
VD=12V	Measurement	Simulation	% Error
IH(mA)	15	15.153	1.0200

Switching Time Characteristic

Evaluation Circuit



Simulation result



Comparison Table

	Measurement	Simulation	%Error
Ton(us)	2	2.0469	2.3450
Toff(us)	70	70.238	0.3400